



STPS30H100CW

HIGH VOLTAGE POWER SCHOTTKY RECTIFIER

MAIN PRODUCT CHARACTERISTICS

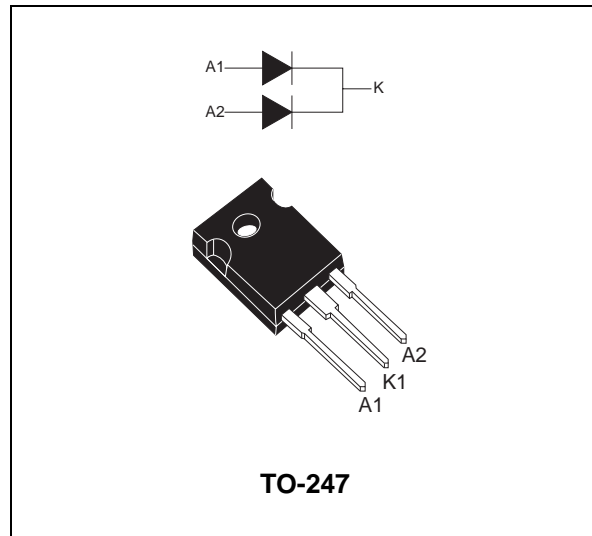
$I_{F(AV)}$	2 x 15 A
V_{RRM}	100 V
$T_j(\text{max})$	175 °C
$V_F(\text{max})$	0.67 V

FEATURES AND BENEFITS

- NEGLIGIBLE SWITCHING LOSSES
- LOW LEAKAGE CURRENT
- GOOD TRADE OFF BETWEEN LEAKAGE CURRENT AND FORWARD VOLTAGE DROP
- LOW THERMAL RESISTANCE
- AVALANCHE RATED

DESCRIPTION

Dual center tap Schottky rectifier suited for Switch Mode Power Supplies and high frequency DC to DC converters. Packaged in TO-247, this device is intended for use in high frequency inverters.



ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter	Value	Unit
V_{RRM}	Repetitive peak reverse voltage	100	V
$I_{F(RMS)}$	RMS forward current	30	A
$I_{F(AV)}$	Average forward current	$T_c = 155^\circ\text{C}$ $\delta = 0.5$ Per diode: 15 Per device: 30	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10 \text{ ms}$ sinusoidal	250 A
I_{RRM}	Repetitive peak reverse current	$t_p = 2 \mu\text{s}$ $F = 1\text{kHz}$ square	1 A
I_{RSM}	Non repetitive peak reverse current	$t_p = 100 \mu\text{s}$ square	3 A
E_{AS}	Non repetitive avalanche energy	$T_j = 25^\circ\text{C}$ $L = 60 \text{ mH}$ $I_{as} = 2 \text{ A}$ per diode	24 mJ
T_{stg}	Storage temperature range	- 65 to + 175	°C
T_j	Maximum operating junction temperature	175	°C
dV/dt	Critical rate of rise of rise voltage	10000	V/ μs

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THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
R _{th(j-c)}	Junction to case		Per diode	°C/W
			Total	
R _{th(c)}	Coupling		0.1	

When the diodes 1 and 2 are used simultaneously :
 $\Delta T_j(\text{diode 1}) = P(\text{diode 1}) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode 2}) \times R_{th(c)}$

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Tests Conditions		Min.	Typ.	Max.	Unit
I _R *	Reverse leakage current	T _j = 25°C	V _R = V _{RRM}			5	μA
		T _j = 125°C			2	6	mA
V _F **	Forward voltage drop	T _j = 25°C	I _F = 15 A			0.80	V
		T _j = 125°C	I _F = 15 A		0.64	0.67	
		T _j = 25°C	I _F = 30 A			0.93	
		T _j = 125°C	I _F = 30 A		0.74	0.80	

Pulse test : * tp = 5 ms, δ < 2%
 ** tp = 380 μs, δ < 2%

To evaluate the maximum conduction losses use the following equation :
 $P = 0.54 \times I_{F(AV)} + 0.0086 \times I_{F(RMS)}^2$

Fig. 1: Average forward power dissipation versus average forward current (per diode).

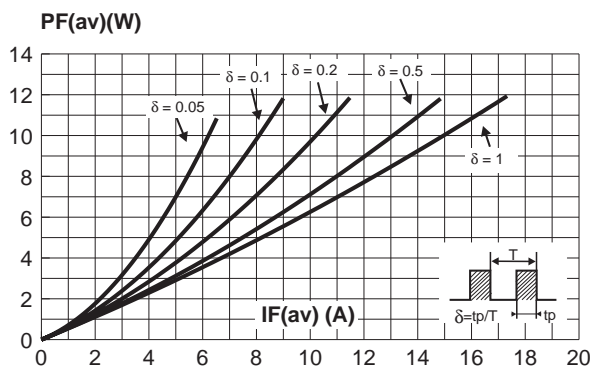


Fig. 2: Average forward current versus ambient temperature (δ=0.5, per diode).

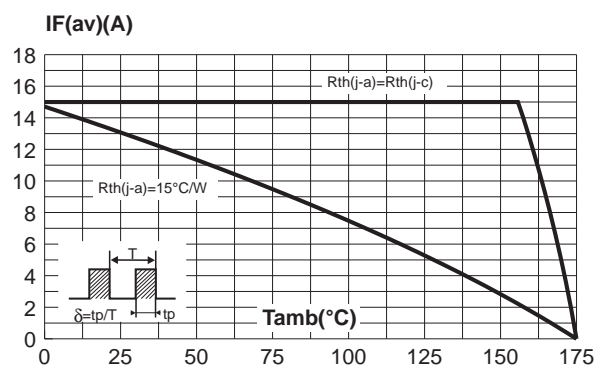


Fig. 3: Non repetitive surge peak forward current versus overload duration (maximum values, per diode).

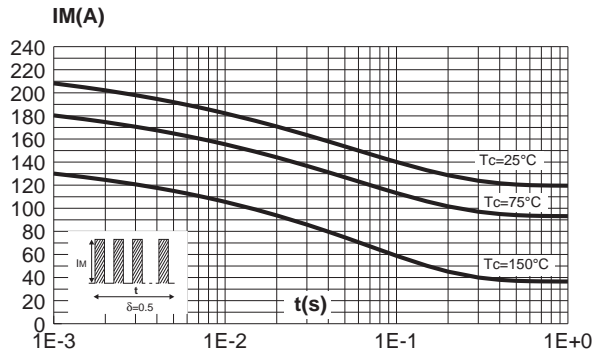


Fig. 4: Relative variation of thermal impedance junction to case versus pulse duration.

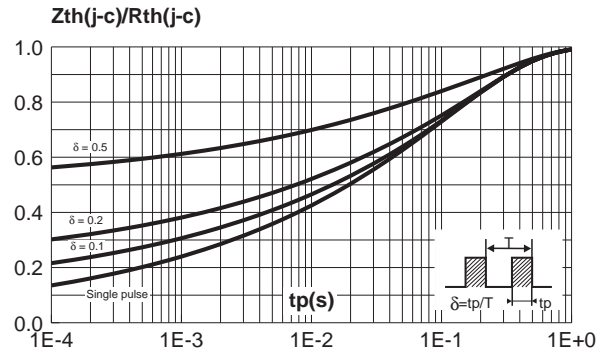


Fig. 5: Reverse leakage current versus reverse voltage applied (typical values, per diode).

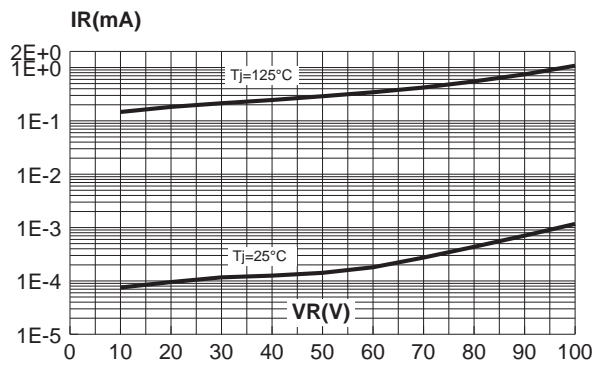


Fig. 6: Junction capacitance versus reverse voltage applied (typical values, per diode).

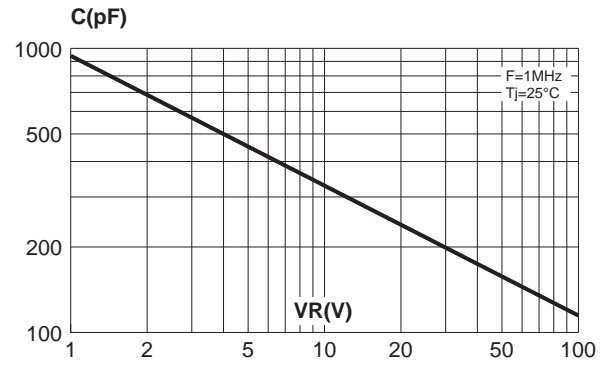
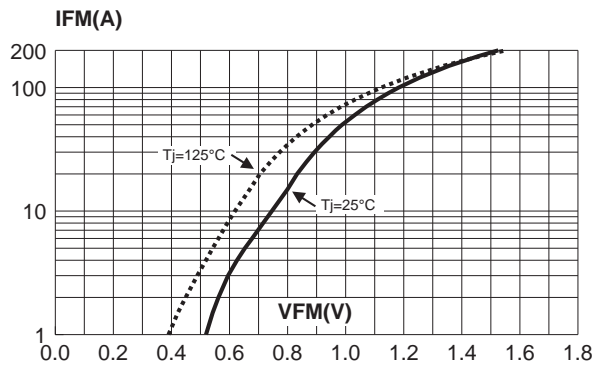
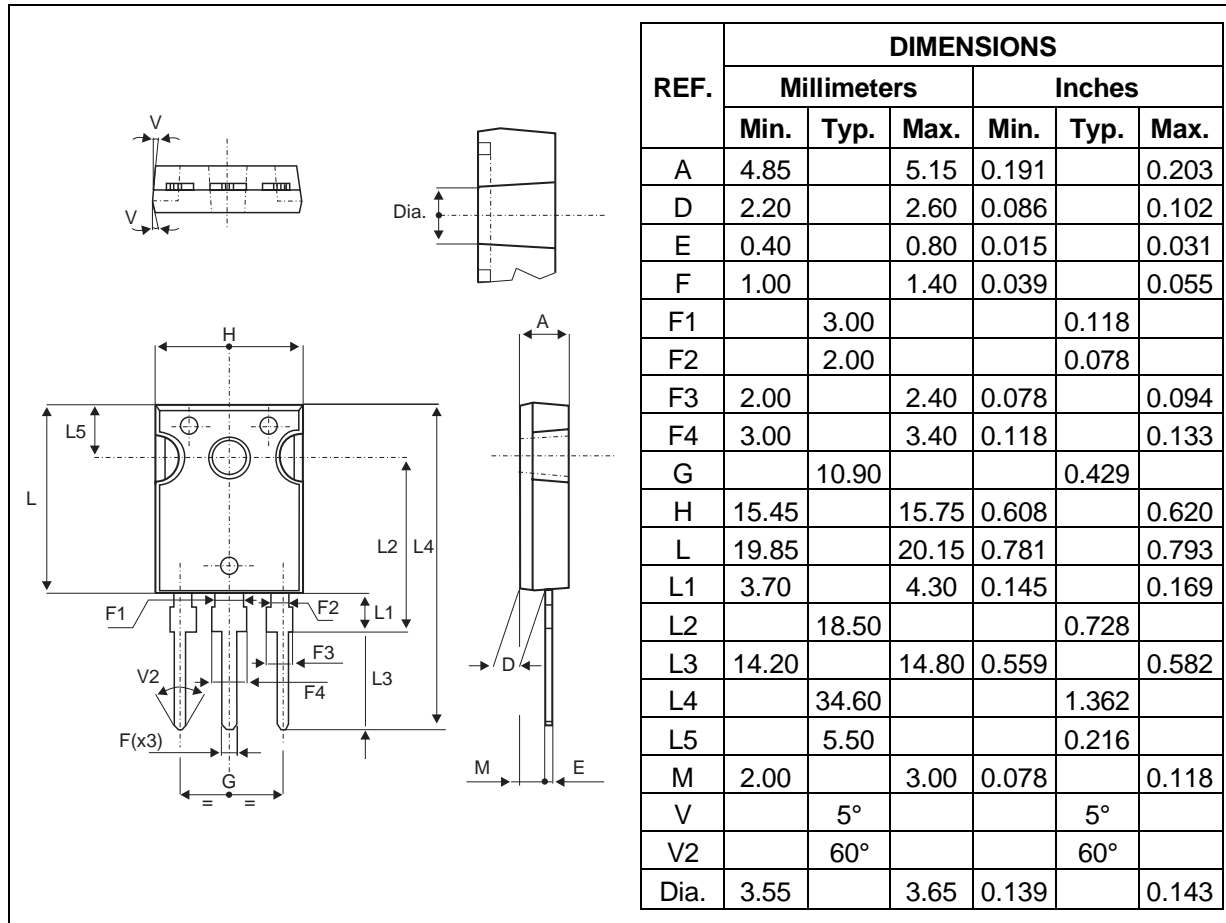


Fig. 7: Forward voltage drop versus forward current (maximum values, per diode).



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PACKAGE MECHANICAL DATA TO-247



- Cooling method: C
- Recommended torque value: 0.8 N.m.
- Maximum torque value: 1 N.m.

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS30H100CW	STPS30H100CW	TO-247	4.36g	30	Tube

- Epoxy meets UL94,V0

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